

ABSTRACT OF THE DISCLOSURE

Low cross talk resistive cross point memory devices are provided, along with methods of manufacture and use. The memory device comprises a bit formed using a perovskite material interposed at a cross point of an upper electrode and lower electrode. Each bit has a resistivity that can change through a range of values in response to application of one, or more, voltage pulses. Voltage pulses may be used to increase the resistivity of the bit, decrease the resistivity of the bit, or determine the resistivity of the bit. Memory circuits are provided to aid in the programming and read out of the bit region.